



The 4th International Workshop on Advanced Materials and Devices

10-13 August, Thai Nguyen, Vietnam

PROGRAM AND ABSTRACTS

The 4th International Workshop on
Advanced Materials and Devices
IWAMD 2023

Program and Abstracts

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		¹ Nano and Energy Center, VNU University of Science, Ha Noi, Vietnam; ² Faculty of Physics, VNU University of Science, Ha Noi, Vietnam
13:50 – 14:10	QMA-15	<i>Magnetic/gold nanocrescents like nano-heater and nano-probe</i> <u>Xuan Hoa Vu</u> , Thi Thu Ha Pham, Emmanuel Fort, Michael Levy, Tran Thu Trang, and Nguyen Van Dang Thai Nguyen University of Sciences, Vietnam
14:10 – 14:30	QMA-16 (online)	<i>Optimization and manipulation of quantum dot based single photon source for quantum applications</i> Gia Long Ngo, Jean-Pierre Hermier, and <u>Ngoc Diep Lai</u> LUMIN, ENS Paris-Saclay, Université Paris-Saclay, France
14:30 – 14:50	QMA-17	<i>Harnessing photonic bound states in the continuum for enhanced light-matter interactions in nanophotonics</i> <u>Son Tung Ha</u> , Mengfei Wu, Ramón Paniagua-Domínguez, Hai Son Nguyen, Cesare Soci, Hilmi Volkan Demir, and Arseniy I. Kuznetsov Institute of Materials Research and Engineering, Agency for Science, Technology and Research, Singapore
14:50 – 15:10	QMA-18 (online)	<i>Novel mechanisms for light-matter interaction using bound states in the continuum</i> <u>Hai Son Nguyen</u> ^{1,2} ¹ Université de Lyon, Ecole Centrale de Lyon, CNRS, INSA Lyon, Université Claude Bernard Lyon 1, CPE Lyon, France; ² Institut Universitaire de France (IUF), France

BIN-2 Chairs: Trinh Chu Duc and Loi Tonthat

13:30 – 13:55	BIN-K2	<i>From microengineering to organ-on-a-chip: An Evolution of Biochip Technology</i> <u>Loc Do Quang</u> ¹ , <u>Hang Nguyen Thu</u> ² , <u>Tung Bui Thanh</u> ² , and <u>Trinh Chu Duc</u> ² ¹ University of Science, Vietnam National University, Hanoi, Vietnam; ² University of Engineering and Technology, Vietnam National University, Hanoi, Vietnam
13:55 – 14:15	BIN-I3	<i>Multifunctional ultrasmall Au-Fe₃O₄ nanoparticles for cancer therapy</i> <u>Loi Tonthat</u> Tohoku University, Japan
14:15 – 14:35	BIN-I4	<i>3D-printing scaffolds with polycaprolactone/collagen/peptide enhance mouse mesenchymal stem vitality and bone regeneration</i> <u>Van-Tinh Nguyen</u> , Gun-Woo Oh, and Won-Kyo Jung VINMEC High-Tech Center, Vietnam
14:35 – 14:55	BIN-I5	<i>SERS detection of phenol on CuO/Au core/shell nanowires</i>

Thi Ha Tran, Minh Phuong Le, Van Tan Tran, Quang Hoa Nguyen, Van Thanh Pham, Cong Doanh Sal, An Bang Ngac, Viet Tuyen Nguyen, and Nguyen Hai Pham

University of Science, Vietnam National University, Hanoi, Vietnam

14:55 – 15:10 BIN-O2

Utilizing response surface methodology for optimizing quercetin loaded niosome by ethanol injection method

Hien Minh Nguyen^{1,2}, Nguyen Thien Han Le^{1,2}, Tran Phuoc Thuan Nguyen^{1,2}, Binh Minh Do^{1,2}, Ngoc Trong Nghia Chau^{1,2}, Tan Thi Pham^{2,3}, and Minh Tri Le^{1,2}

¹School of Medicine, Vietnam National University Ho Chi Minh City, Vietnam;

²Vietnam National University Ho Chi Minh City (VNUHCM), Vietnam; ³Ho Chi Minh City University of Technology (HCMUT), Ho Chi Minh City, Vietnam

EMD-3 Chairs: Nguyen Quang Chinh and Susumu Horita

13:30 – 13:55 EMD-K3

Sustainable Graphene production, ink formulations and printing advanced chemoresitive sensing devices

Tran T. Tung, Kamrul Hassan, Anh Tuan Tran, Ramesh K, Ehab Mohamed A. E. Salih, and Dusan Losic

School of Chemical Engineering, The University of Adelaide, South Australia

13:55 – 14:15 EMD-I5

Ultrafine-grained metals: Their advantages in the use of micro-devices and description of grain size strengthening by a modified Hall-Petch equation

Nguyen Quang Chinh

Eötvös Loránd University, Budapest, Hungary

14:15 – 14:35 EMD-I6

Creating, reading, and deleting Skyrmions in a magnetic tunnel junction

Shaohai Chen

Institute of Materials Research & Engineering, Agency for Science, Technology & Research (A*STAR), Singapore

14:35 – 14:55 EMD-I7

Effect of ammonia gas in annealing process on reduction of residual OH-bonds and improvement of electrical properties of low-temperature silicon oxide films

Susumu Horita

Japan Advanced Institute of Science and Technology, Japan

14:55 – 15:10 EMD-O3

A first principles analysis on the effects of AGNR passivation towards adsorption of Hydrogen atoms

Kyle Alfred Paz, Al Rey Villagracia, and Melanie David

De La Salle University, Philippines

EMD-4 Chairs: Peng Song and Shin-Ichiro Kuroki

13:30 – 13:50 EMD-I8

SiC CMOS integrated circuits and image sensors for extreme environment applications

Van Son¹, Dinh Khanh Manh¹, Nguyen Thi Yen Lan¹, Ngo Duy Minh¹,
Do Xuan Hai², Than Thi Trang Uyen³, Hoang Thi My Nhun¹, and
Nguyen Hoang Nam¹

¹VNU University of Science, Vietnam; ²Vietnam Military Medical University, Vietnam; ³Vinmec Hightech Center, Vinmec, Vietnam

09:35 – 09:50 BIN-O5

A novel nanoemulsion in ethanol-water solution using Trisodium citrate as emulsifying agent: formation and application in Si-QD/SiO₂ and NiFe₂O₄/SiO₂ core-shell structure synthesis

Phi Thi Huong¹, Hoang V. Huy¹, Doan H. Anh², Nguyen H. Nam¹, Tran T. Hong³, and Luu M. Quynh²

¹Nano and Energy Center, VNU University of Science, Hanoi, Vietnam; ²Faculty of Physics, VNU University of Science, Hanoi, Vietnam; ³Faculty of Environmental Sciences, VNU University of Science, Hanoi, Vietnam

09:50 – 10:05 BIN-O6

Understanding mechanism of photo-induced enhanced Raman scattering on ZnO/Au nanorods

Van Tan Tran, Minh Phuong Le, Quang Hoa Nguyen, Van Thanh Pham, Cong Doanh Sai, Nguyen Hai Pham, Viet Tuyen Nguyen, Thi Ha Tran, and An Bang Ngac

University of Science, Vietnam National University, Hanoi, Vietnam

10:05 – 10:20 BIN-O7

Investigation of the remineralization ability of biphasic calcium phosphate in artificial saliva

Nhi-Thao Ngoc Dang^{1,2} and Thi-Hiep Nguyen^{1,2}

¹International University, Vietnam; ²Vietnam National University, Ho Chi Minh City, Vietnam

EMD-7 Chairs: Takehito Nakano and Ivan Škorvánek

08:30 – 08:50 EMD-I16

Non-volatile multi-state switching of magnetisation states induced by electric-field-driven in an micropatterned multiferroics

Do Thi Huong Giang, Vu Nguyen Thuc, Ho Anh Tam, Nguyen Van Tuan, Nguyen Thi Ngoc, Van-Hai Dinh, Le Van Lich, and Nguyen Huu Duc
VNU University of Engineering and Technology, Vietnam National University, Hanoi, Vietnam

08:50 – 09:10 EMD-I17

Neutron diffraction studies on s- and p-electron magnets

Takehito Nakano
Ibaraki University, Japan

09:10 – 09:30 EMD-I18

Ultra-rapidly annealed Ni-rich nanocrystalline Fe-Ni-Nb-B alloys with excellent magnetic softness

Ivan Škorvánek¹, Jozef Marcin¹, Branislav Kunca¹, and Peter Švec²
¹Institute of Experimental Physics, Slovak Academy of Sciences, Slovakia;
²Institute of Physics, Slovak Academy of Sciences, Slovakia

09:30 – 09:45 EMD-O9

Exploration of transition metal oxides-based analog memristors with self-rectifying characteristics for artificial synaptic applications

poly(glycosylated methacrylate) polymer complex.

Growth of well aligned ZnO nanorods by hydrothermal method

References:

1) T. H. Tran, T. H. Dinh, T. H. Trang Bui, M. Phuong Le, V. T. Tran, Q. Hoa Nguyen, V. T. Pham, C. Doanh Sai, A. Bang Ngac, V. Tuyen Nguyen*, and N. H. Pham

3) Q. Wartburg, *Science*, 225, 309-314 (1984).

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In this work, well aligned ZnO nanorods were grown by a facile hydrothermal process. In the first stage, ZnO nanocrystalline thin films were prepared by dip coating method. The prepared ZnO thin films were used as seed layer for the growth of ZnO nanorods in the second stage. The effect of thermal annealing of seed layer on the morphology and structures of the ZnO nanorods were investigated.

Keywords: CuO nanowires, core/shell structures, sputtering, surface enhanced Raman scattering (SERS).

1. Introduction

2. Experimental

3. Results and discussion

4. Conclusion

5. Acknowledgements

6. References

7. Author biography

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